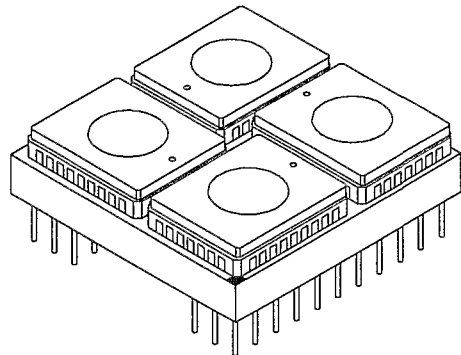


DESCRIPTION:

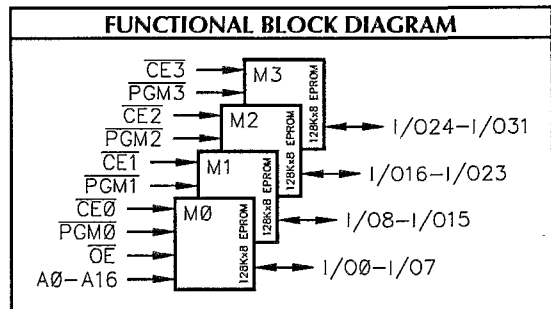
The DPV12832VA is a 66-pin Pin Grid Array (PGA) consisting of four 128K X 8 UVEPROM devices in ceramic LCC packages surface mounted on a co-fired ceramic substrate with matched thermal coefficients. The LCCs are mounted in a rotary pattern resulting in the smallest possible module outline.

The pins have been arranged around a central 0.6" gap which can accommodate a heat rail, if desired. In this central gap is a cavity containing four 0.1µf decoupling capacitors.



FEATURES:

- Organizations Available:
512K X 8, 256K X 16 or 128K X 32
- Access Times:
120, 150, 170, 200, 250ns
- Fully Static Operation - No clock or refresh required
- Programming Voltage 13.0 Vdc
- Simple Programming Requirements
- Three-State Outputs
- High Speed Programming Algorithm (100µs Pulses Typ.)
- Common Data Inputs and Outputs
- Power Consumption:
22mW (Standby)
1.1W (Active)
- TTL-compatible Inputs and Outputs
- 66-Pin PGA (Pin Grid Array) Package
- Same Package as other Versapac Versions (EEPROM, SRAM and MIXED)
- Module Weight is 15 grams



PIN NAMES	
A0 - A16	Address Inputs
I/O0 - I/O31	Data In/Out
CE0 - CE3	Chip Enables
PGM0 - PGM3	Program Enables
OE	Output Enable
VDD	Power (+5V)
VSS	Ground
VPP	Programming Voltage
N.C.	No Connect

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PIN-OUT DIAGRAM

1 I/O8	12 PGM1	23 I/O15	34 I/O24	45 VDD	56 I/O31
2 I/O9	13 CE1	24 I/O14	35 I/O25	46 CE3	57 I/O30
3 I/O10	14 VSS	25 I/O13	36 I/O26	47 PGM3	58 I/O29
4 A13	15 I/O11	26 I/O12	37 A6	48 I/O27	59 I/O28
5 A14	16 A10	27 OE	38 A7	49 A3	60 A0
6 A15	17 A11	28 N.C.	39 VPP	50 A4	61 A1
7 A16	18 A12	29 PGM0	40 A8	51 A5	62 A2
8 N.C.	19 VDD	30 I/O7	41 A9	52 PGM2	63 I/O23
9 I/O0	20 CE0	31 I/O6	42 I/O16	53 CE2	64 I/O22
10 I/O1	21 N.C.	32 I/O5	43 I/O17	54 VSS	65 I/O21
11 I/O2	22 I/O3	33 I/O4	44 I/O18	55 I/O19	66 I/O20

(TOP VIEW)

ABSOLUTE MAXIMUM RATINGS ¹			
Symbol	Parameter	Value	Unit
T _{STG}	Storage Temperature	-65 to +125	°C
T _{BIAS}	Temperature Under Bias	-55 to +125	°C
V _{DD}	Supply Voltage ²	-0.5 to +7.0	V
V _{I/O}	Input/Output Voltage ²	-0.5 to +7.0	V
V _{PP}	Programming Voltage ²	-0.5 to +13.0	V

RECOMMENDED OPERATING RANGE ²					
Symbol	Characteristic	Min.	Typ.	Max.	Unit
V _{DD}	Supply Voltage ⁴	4.5	5.0	5.5	V
V _{IH}	Input HIGH Voltage	2.2		V _{DD} +1.0	V
V _{IL}	Input LOW Voltage	-0.2		0.8	V
V _{PP}	V _{PP} Supply Voltage ⁵	12.75	13.0	13.25	V

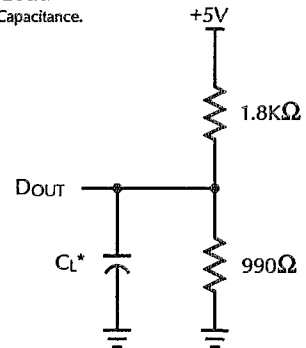
CAPACITANCE ³ : T _A = 25°C, F = 1.0MHz				
Symbol	Parameter	Max.	Unit	Condition
C _{CE}	Chip Enable	15	pF	V _{IN} = 0V
C _{ADR}	Address Input	50		
C _{OE}	Output Enable	50		
C _{I/O}	Data Input/Output	25		

AC TEST CONDITIONS: Including Programming	
Input Pulse Levels	0V to 3.0V
Input Pulse Rise and Fall Time	≤ 20ns
Input Timing Reference Levels	1.5V
Output Timing Reference Levels	1.5V

Output Load		
Float	C _L	Parameters Measured
1	100 pF	except t _{DF} and t _{DFP}
2	5 pF	t _{DF} and t _{DFP}

Figure 1. Output Load

* Including Scope and Jig Capacitance.



DC OPERATING CHARACTERISTICS ⁶ : Over operating ranges									
Symbol	Characteristics	Test Conditions	X8		X16		X32		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	
I _{IN}	Input Leakage Current	V _{IN} = V _{DD}	-20	20	-20	20	-20	20	μA
I _{OUT}	Output Leakage Current	CE = V _{IH} , V _{IN} = V _{DD} or V _{SS}	-40	40	-20	20	-10	10	μA
I _{CC}	V _{DD} Operation Current, Read	V _{IN} = V _{IH} or V _{IL} , I _{OUT} = 0mA Cycle = min. Duty = 100%		50		100		200	mA
I _{SB1}	V _{DD} Standby Current (TTL)	CE = V _{IH} , V _{IN} = V _{IH} or V _{IL}		4		4		4	mA
I _{SB2}	V _{DD} Standby Current (CMOS)	CE = V _{DD} ± 0.3V V _{IN} ≥ V _{DD} - 3.0V or V _{IN} ≤ 0.3V		400		400		400	μA
I _{PP1}	V _{PP} Supply Current Programming	CE, = V _{IL} , OE = V _{IH} , T _A = 25°C		20		40		80	mA
I _{PP3}	V _{PP} Supply Current Read ⁴	CE, OE = V _{IL} , I _{OUT} > 0mA		40		40		40	μA
V _{OL}	Output LOW Voltage	I _{OUT} = 2.1mA		0.45		0.45		0.45	V
V _{OH1}	Output HIGH Voltage	I _{OUT} = -400μA	2.4		2.4		2.4		V
V _{IL}	Input LOW Level		-0.2	0.8	-0.2	0.8	-0.2	0.8	V
V _{IH}	Input HIGH Level		2.0	V _{DD} +5	2.0	V _{DD} +5	2.0	V _{DD} +5	V

FUNCTIONS AND PIN CONNECTIONS							
Mode	Function	\overline{CE}	\overline{OE}	\overline{PGM}	V_{PP}	V_{DD}	I/O0-I/O31
Read Operations	Read	L	L	X	5V	5V	Data Out
	Output Deselect	X	H	X			High Impedance
	Standby	H	X	X			High Impedance
Program Operations ($T_A = +25 \pm 5^\circ\text{C}$)	Program	L	H	L	13.0V	6.5V	Data In
	Program Inhibit	H	X	X			High Impedance
	Program Verify	L	L	H			Data Out

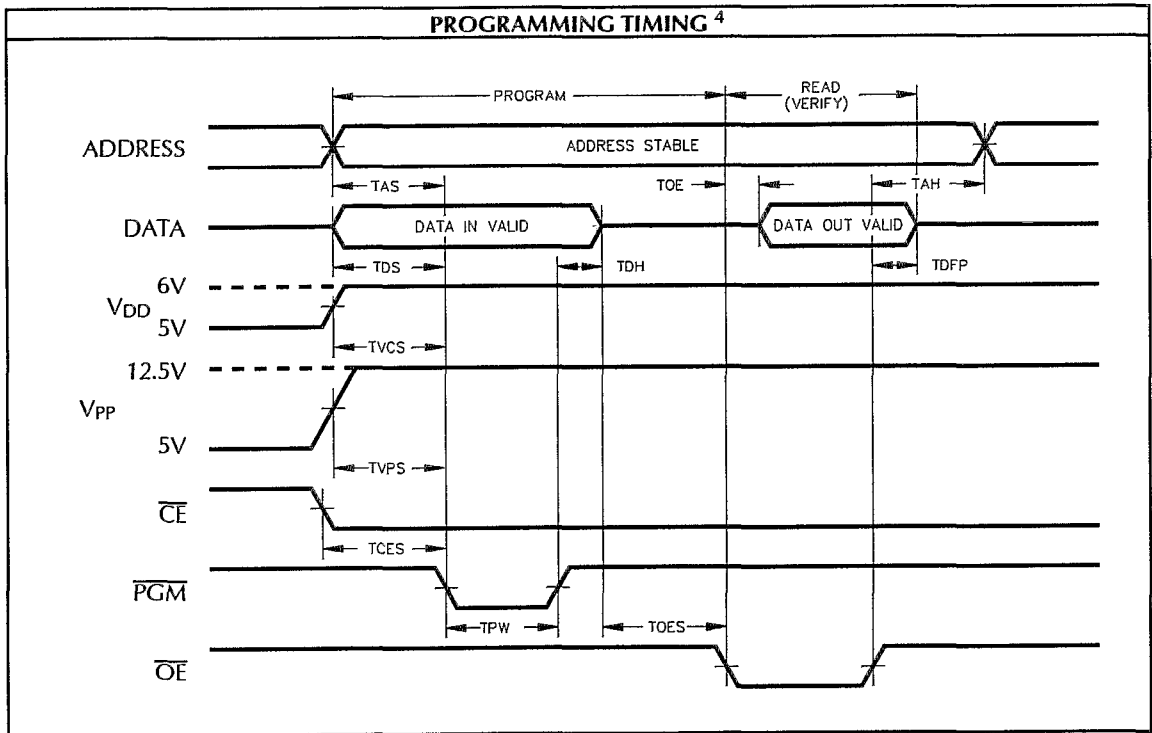
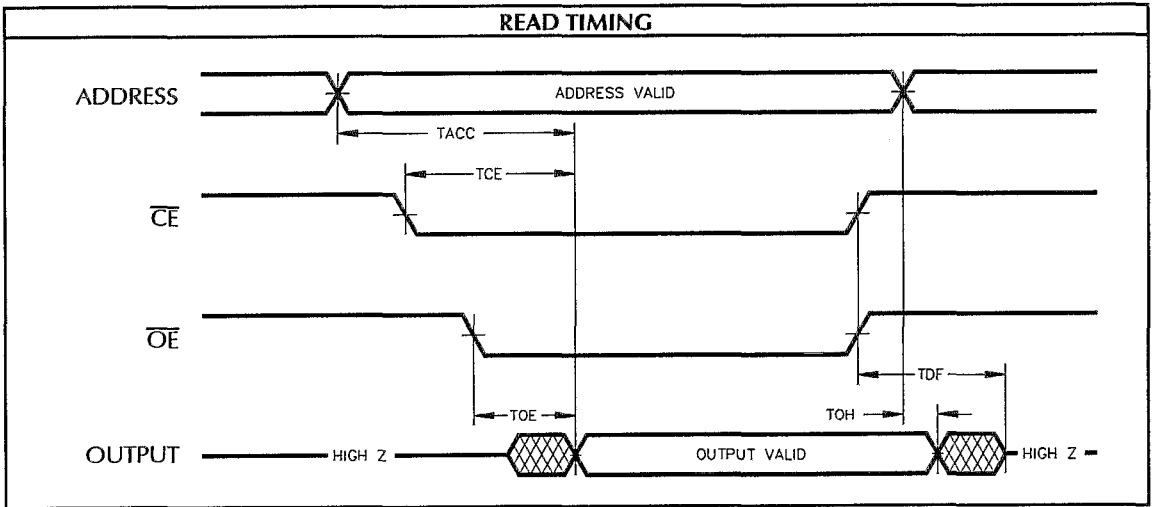
L = LOW, H = HIGH and X = Don't Care

AC OPERATING CONDITIONS AND CHARACTERISTICS - READ: Over operating ranges													
No.	Symbol	Parameter	-120		-150		-170		-200		-250		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
1	t_{ACC}	Address Access Time ⁸		120		150		170		200		250	ns
2	t_{CE}	Chip Enable to Output Valid ⁷		120		150		170		200		250	ns
3	t_{OE}	Output Enable to Output Valid ^{7, 8}		35		40		65		75		100	ns
4	t_{DF}	\overline{OE} or \overline{CE} HIGH to Output Float ^{3, 9}	0	35	0	40	0	50	0	60	0	60	ns
5	t_{OH}	Output Hold from Address Change	0		0		0		0		0		ns

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AC PROGRAMMING CONDITIONS AND CHARACTERISTICS: Over operating ranges					
No.	Symbol	Parameter	Min.	Max.	Unit
6	t_{AS}	Address Set-up Time	2		μs
7	t_{CES}	Chip Enable Set-up Time	2		μs
8	t_{OES}	Output Enable Set-up Time	2		μs
9	t_{DS}	Data Set-up Time	2		μs
10	t_{VCS}	V_{DD} Set-up Time ⁵	2		μs
11	t_{VPS}	V_{PP} Set-up Time ⁵	2		μs
12	t_{AH}	Address Hold Time	0		μs
13	t_{DH}	Data Hold Time	2		μs
14	t_{DFP}	Output Enable HIGH Output Float Delay ³	0	130	ns
15	t_{PW}	Programming Pulse Width ¹⁰	95	105	μs
16	t_{OE}	Data Valid from Output Enable		150	ns





PROGRAMMING AND ERASING INFORMATION

Programming

Upon delivery from Dense-Pac, or after erasure (See *Erasure section*), the DPV12832VA contains "1's" in every location, and read data is in the high state. "0's" are written into the DPV12832VA through the procedure of programming. A 0.1 μ F capacitor between V_{PP} and V_{SS} is required to prevent excessive voltage transients during programming which could damage the device. Programming modes require +6.5V and +13.0V to be applied to V_{DD} and V_{PP} respectively.

Individual bytes or address locations can be selected and programmed by using the programming algorithm shown in Figure 2. In the programming mode, \overline{CE} is set at V_{IL} , \overline{OE} is set at V_{IH} , V_{DD} is set at +6.5V, and V_{PP} is set at +13.0V. After the applied address and input data signals are stable, programming is accomplished by a 100 μ s V_{IL} pulse on the \overline{PGM} pin (refer to the *Programming Timing Diagram*).

First program each address with a 100 μ s pulse on the \overline{PGM} without verification. Then return to first address and start a verification loop verifying each address. If an address location fails verification, apply up to 10 consecutive 100 μ s \overline{PGM} pulses with a verification after each pulse.

If the device fails to program after 10 attempts, the programming is considered failed. After the byte is verified, continue the algorithm through all the required addresses. Then lower V_{DD} and V_{PP} to +5.0Vdc and compare the data programmed with the original data to determine if the device passes. A programming adapter for programming on standard EPROM programmers is available, contact Dense-Pac sales for more information.

Erasure

To clear all locations of their programmed contents it is necessary to expose the DPV12832VA to an ultraviolet light source. A dosage of 15W-seconds/cm² is required to completely erase a DPV12832VA. This dosage can be obtained by exposure to an ultraviolet lamp [wavelength of 2537 Angstroms (Å) with an intensity of 12,000 μ W/cm²] for 20 minutes.

The DPV12832VA and similar devices can be erased by light sources having wavelengths shorter than 4000Å. Although erasure time will be much longer than with UV sources at 2537Å, nevertheless the exposure to fluorescent light or sunlight will eventually erase the DPV12832VA. After programming, the package windows should be covered by an opaque label or substance, to prevent inadvertent erasure.

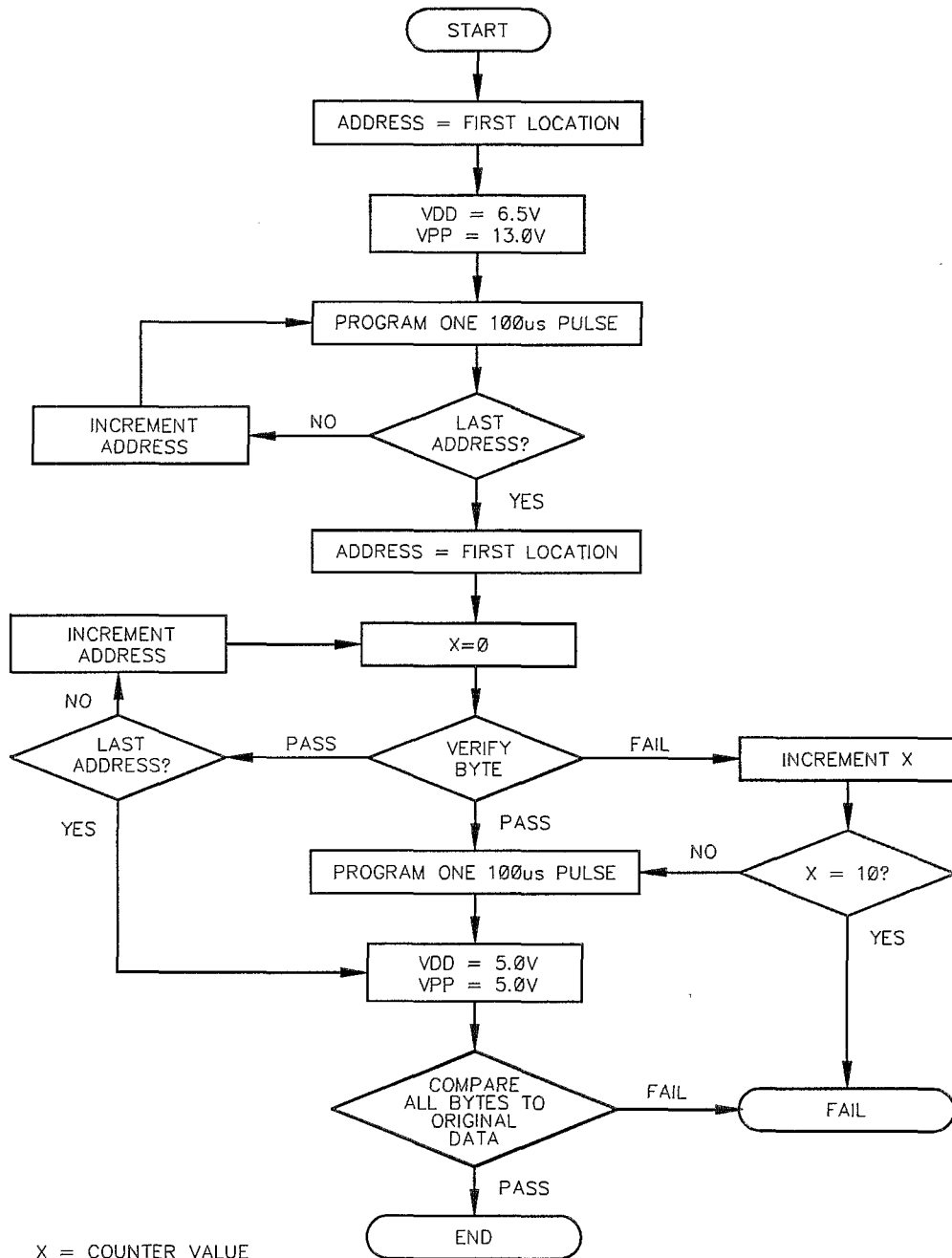
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NOTES:

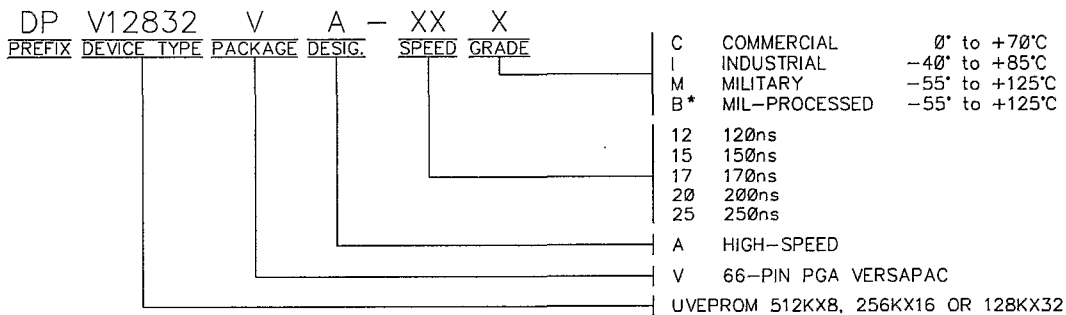
1. Stresses greater than those listed under **ABSOLUTE MAXIMUM RATINGS** may cause permanent damage to the device. This is stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. All voltages are with respect to V_{SS} .
3. This parameter is guaranteed and not 100% tested.
4. V_{DD} must be applied either coincident with or before V_{PP} and removed either coincident with or after V_{PP} .
5. V_{PP} must not be greater than 14.0V including overshoot. Permanent device damage may occur if the device is taken out or put into socket with $V_{PP} = 13.0V$. Also, during $\overline{CE} = V_{IL}$, V_{PP} must not be switched from 5.0V to 13.0V or vice-versa.
6. $t_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$, $V_{DD} = 5.0V \pm 0.5V$, and $V_{PP} = V_{DD}$ reading. $t_A = +25^\circ\text{C} \pm 5^\circ\text{C}$, $V_{DD} = 6.5V \pm 0.25V$, $V_{PP} = 13.0V \pm 0.25V$ programming.
7. \overline{OE} may be delayed up to t_{CE-TOE} after the following edge of \overline{CE} without impact on t_{CE} .
8. \overline{OE} may be delayed up to $t_{ACC-TOE}$ after the following Address is valid without impact on t_{ACC} .
9. t_{DF} is specified from \overline{OE} or \overline{CE} , whichever occurs first.
10. Program Pulse Width Tolerance is 100 μ s \pm 5%.



Figure 2. Programming Flow Chart

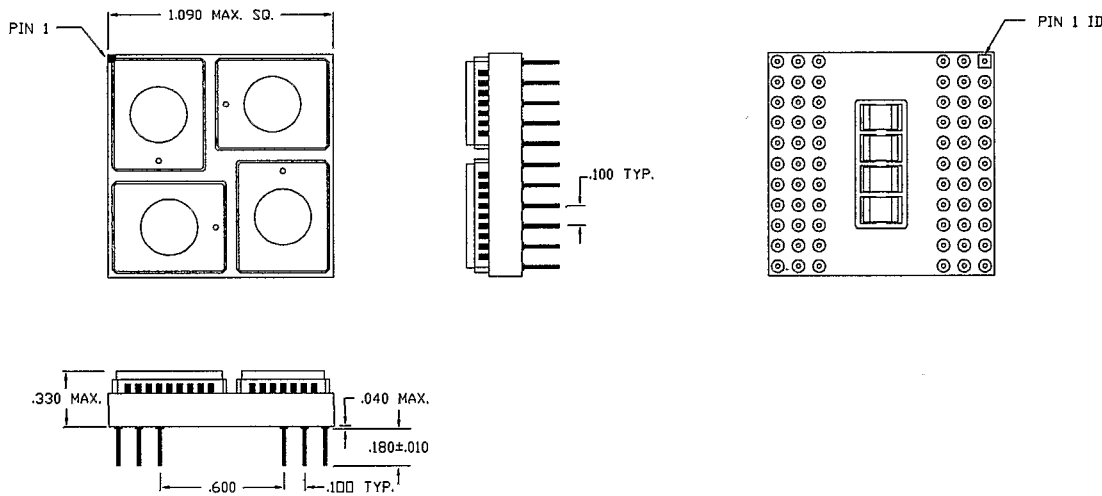


ORDERING INFORMATION



* B grade modules are constructed with 883 devices.

MECHANICAL DIAGRAMS



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